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April 2015

FDC5614P

60V P-Channel Logic Level PowerTrench® MOSFET

General Description

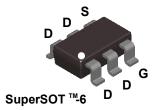
This 60V P-Channel MOSFET uses Fairchild's high voltage PowerTrench process. It has been optimized for power management applications.

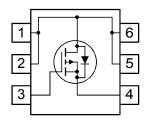
Applications

- DC-DC converters
- Load switch
- · Power management

Features

- -3 A, -60 V. $R_{DS(ON)} = 0.105 \Omega @ V_{GS} = -10 V$ $R_{DS(ON)} = 0.135 \Omega @ V_{GS} = -4.5 V$
- · Fast switching speed
- High performance trench technology for extremely low $R_{\mbox{\scriptsize DS}(\mbox{\scriptsize ON})}$





Absolute Maximum Ratings T_A=25°C unless otherwise noted

Symbol	Parameter		Ratings	Units
V _{DSS}	Drain-Source Voltage		-60	V
V_{GSS}	Gate-Source Voltage		±20	V
I _D	Drain Current - Continuous	(Note 1a)	-3	А
	- Pulsed		-20	
P _D	Maximum Power Dissipation	(Note 1a)	1.6	W
		(Note 1b)	0.8	
T _J , T _{STG}	Operating and Storage Junction Tem	perature Range	-55 to +150	°C

Thermal Characteristics

$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	(Note 1a)	78	°C/W
R _{θJC}	Thermal Resistance, Junction-to-Case	(Note 1)	30	°C/W

Package Marking and Ordering Information

_	Device Marking	Device	Reel Size	Tape width	Quantity
_	.564	FDC5614P	7"	8mm	3000 units

Symbol	Parameter	Test Conditions	Min	Тур	Max	Units
Off Char	acteristics		I	I	I	ı
BV _{DSS}	Drain–Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, I_{D} = -250 \mu\text{A}$	-60			V
ΔBV _{DSS} ΔT _J	Breakdown Voltage Temperature Coefficient	I_D = -250 μ A, Referenced to 25°C		-49		mV/°C
I _{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = -48 \text{ V}, V_{GS} = 0 \text{ V}$			-1	μΑ
I _{GSSF}	Gate–Body Leakage, Forward	$V_{GS} = 20V$, $V_{DS} = 0 V$			100	nA
I _{GSSR}	Gate–Body Leakage, Reverse	V _{GS} = -20 V V _{DS} = 0 V			-100	nA
On Char	acteristics (Note 2)					
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	-1	-1.6	-3	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate Threshold Voltage Temperature Coefficient	I_D = -250 μ A,Referenced to 25°C		4		mV/°C
R _{DS(on)}	Static Drain–Source On–Resistance	$V_{GS} = -10 \text{ V}, I_D = -3 \text{ A}$ $V_{GS} = -4.5 \text{ V}, I_D = -2.7 \text{ A}$ $V_{GS} = -10 \text{ V}, I_D = -3 \text{ A} \text{ T}_J = 125^{\circ}\text{C}$		82 105 130	105 135 190	mΩ
I _{D(on)}	On–State Drain Current	$V_{GS} = -10 \text{ V}, I_D = -3 \text{ A T}_J = 125^{\circ}\text{C}$ $V_{GS} = -10 \text{ V}, V_{DS} = -5 \text{ V}$	-20			Α
g FS	Forward Transconductance	$V_{DS} = -5 \text{ V}, \qquad I_{D} = -3 \text{ A}$		8		S
Dynamic	Characteristics		•	•		•
C _{iss}	Input Capacitance	$V_{DS} = -30 \text{ V}, V_{GS} = 0 \text{ V},$		759		pF
Coss	Output Capacitance	f = 1.0 MHz		90		pF
C _{rss}	Reverse Transfer Capacitance			39		pF
Switchir	g Characteristics (Note 2)					
t _{d(on)}	Turn-On Delay Time	$V_{DD} = -30 \text{ V}, \qquad I_{D} = -1 \text{ A},$		7	14	ns
t _r	Turn-On Rise Time	$V_{GS} = -10 \text{ V}, \qquad R_{GEN} = 6 \Omega$		10	20	ns
$t_{d(off)}$	Turn-Off Delay Time	7		19	34	ns
t _f	Turn-Off Fall Time	7		12	22	ns
Q_g	Total Gate Charge	$V_{DS} = -30V$, $I_{D} = -3.0 A$,		15	24	nC
Q_{gs}	Gate-Source Charge	V _{GS} = -10 V		2.5		nC
Q_{gd}	Gate-Drain Charge			3.0		nC
Drain-S	ource Diode Characteristics	and Maximum Ratings				
Is	Maximum Continuous Drain–Source				-1.3	Α
V _{SD}	Drain–Source Diode Forward Voltage	$V_{GS} = 0 \text{ V}, I_S = -1.3 \text{ A} \text{(Note 2)}$		-0.8	-1.2	V

Notes

- a. 78°C/W when mounted on a 1in² pad of 2oz copper on FR-4 board.
- b. 156°C/W when mounted on a minimum pad.
- 2. Pulse Test: Pulse Width $\leq 300~\mu s,~Duty~Cycle \leq 2.0\%$

R_{0JA} is the sum of the junction-to-case and case-to-ambient resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. R_{0JC} is guaranteed by design while R_{0CA} is determined by the user's board design.

Typical Characteristics

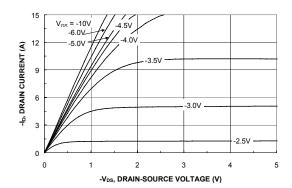


Figure 1. On-Region Characteristics.

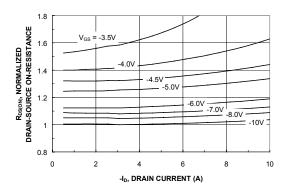


Figure 2. On-Resistance Variation with Drain Current and Gate Voltage.

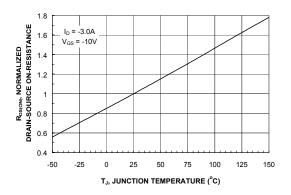


Figure 3. On-Resistance Variation with Temperature.

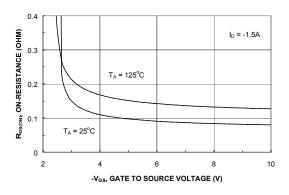


Figure 4. On-Resistance Variation with Gate-to-Source Voltage.

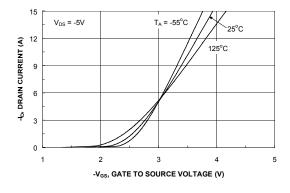


Figure 5. Transfer Characteristics.

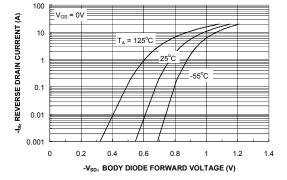
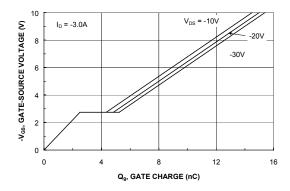


Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature.

Typical Characteristics



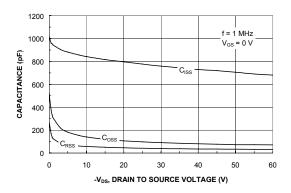
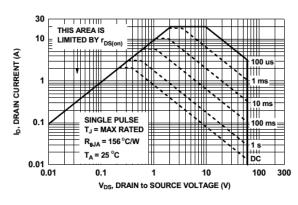


Figure 7. Gate Charge Characteristics.

Figure 8. Capacitance Characteristics.



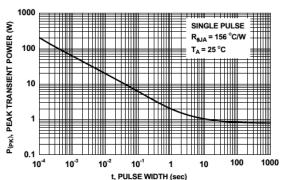
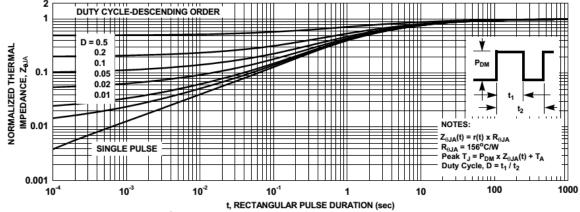
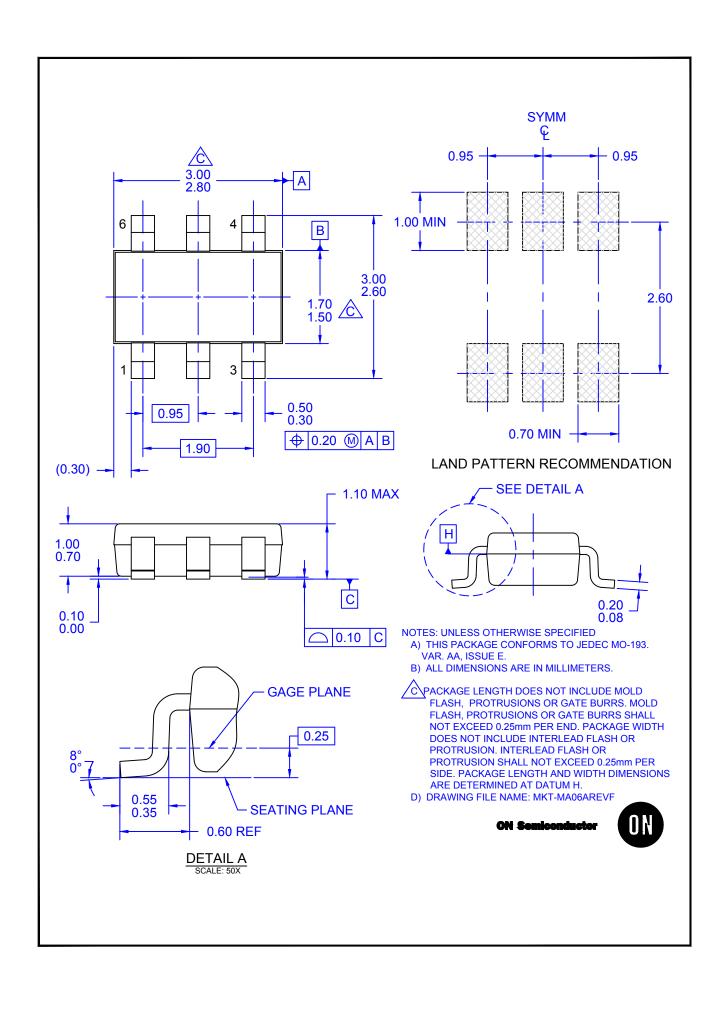


Figure 9. Maximum Safe Operating Area.

Figure 10. Single Pulse Maximum Power Dissipation.



Thermal characterization performed using the conditions described in Note 1b. Transient themal response will change depending on the circuit board design.



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